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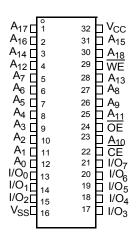
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## **Pin Configuration**

Figure 1. 32-pin SOIC pinout

Top View



## **Product Portfolio**

				Power Dissipation								
Product	Range V <sub>CC</sub> Range (V)		V <sub>CC</sub> Range (V)		Speed		Operating	I <sub>CC</sub> (mA)		Standby	Ι. (Δ)	
Floudet	Range				(ns)	f = 1 MHz		f = 1 MHz f = f <sub>max</sub>		max	Standby I <sub>SB2</sub> (μA)	
		Min	<b>Typ</b> <sup>[2]</sup>	Max		<b>Typ</b> <sup>[2]</sup>	Max	<b>Typ</b> <sup>[2]</sup>	Max	<b>Typ</b> <sup>[2]</sup>	Max	
CY62148DV30LL	Industrial	2.2	3.0	3.6	55	1.5	3	8	10	2	8	

#### Note

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<sup>2.</sup> Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at  $V_{CC} = V_{CC(typ)}$ ,  $T_A = 25$  °C.



## **Maximum Ratings**

DC input voltage [3, 4]0.3 V to V <sub>CC(max)</sub> + 0.3 V
Output current into outputs (LOW)20 mA
Static discharge voltage (per MIL-STD-883, method 3015)
Latch-up current> 200 mA

## **Operating Range**

Product	Range	Ambient Temperature	<b>V</b> <sub>CC</sub> <sup>[5]</sup>
CY62148DV30LL	Industrial	–40 °C to +85 °C	2.2 V to 3.6 V

#### **Electrical Characteristics**

Over the Operating Range

D	Description	Tant 0.		55 ns			11!4
Parameter	Description	lest Co	nditions	Min	<b>Typ</b> [2]	Max	Unit
V <sub>OH</sub>	Output HIGH voltage	I <sub>OH</sub> = -0.1 mA	V <sub>CC</sub> = 2.20 V	2.0	_	_	V
		$I_{OH} = -1.0 \text{ mA}$	V <sub>CC</sub> = 2.70 V	2.4	_	_	V
V <sub>OL</sub>	Output LOW voltage	I <sub>OL</sub> = 0.1 mA	V <sub>CC</sub> = 2.20 V	_	_	0.4	V
		I <sub>OL</sub> = 2.1 mA	V <sub>CC</sub> = 2.70 V	_	_	0.4	V
V <sub>IH</sub>	Input HIGH voltage	V <sub>CC</sub> = 2.2 V to 2.	7 V	1.8	_	V <sub>CC</sub> + 0.3	V
		$V_{CC} = 2.7 \text{ V to } 3.0$	6 V	2.2	_	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	Input LOW voltage	V <sub>CC</sub> = 2.2 V to 2.	7 V	-0.3	_	0.6	V
		$V_{CC} = 2.7 \text{ V to } 3.0$	6 V	-0.3	_	0.8	V
I <sub>IX</sub>	Input leakage current	$GND \le V_1 \le V_{CC}$		<b>–</b> 1	_	+1	μΑ
I <sub>OZ</sub>	Output leakage current	$GND \le V_O \le V_{CC}$	output disabled	<b>–</b> 1	_	+1	μΑ
I <sub>CC</sub>	V <sub>CC</sub> operating supply current	$f = f_{max} = 1/t_{RC}$	$V_{CC} = V_{CC(max)}$		8	10	mA
		f = 1 MHz	I <sub>OUT</sub> = 0 mA CMOS levels	_	1.5	3	mA
I <sub>SB1</sub>	Automatic CE Power-down current – CMOS inputs	$\overline{\text{CE}} \ge \text{V}_{\text{CC}} - 0.2 \text{ V},$ $\text{V}_{\text{IN}} \ge \text{V}_{\text{CC}} - 0.2 \text{ V}, \text{V}_{\text{IN}} \le 0.2 \text{ V}),$ $\text{f} = \text{f}_{\text{max}} \text{ (address and data only)},$ $\text{f} = 0  (\overline{\text{OE}}, \text{ and } \overline{\text{WE}}), \text{V}_{\text{CC}} = 3.60 \text{ V}$		-	2	8	μА
I <sub>SB2</sub>	Automatic CE Power-down current – CMOS inputs	$\overline{\text{CE}} \ge \text{V}_{\text{CC}} - 0.2 \text{ V}$ $\text{V}_{\text{IN}} \ge \text{V}_{\text{CC}} - 0.2 \text{ V}$ $\text{f} = 0, \text{V}_{\text{CC}} = 3.60$	′ or V <sub>IN</sub> <u>≤</u> 0.2 V,	-	2	8	μА

#### Notes

- 3.  $V_{IL(min)} = -2.0 \text{ V}$  for pulse durations less than 20 ns.
- 4.  $V_{IH(max)} = V_{CC} + 0.75 \text{ V for pulse durations less than 20 ns.}$
- 5. Full device AC operation assumes a 100  $\mu$ s ramp time from 0 to  $V_{CC(min)}$  and 200  $\mu$ s wait time after  $V_{CC}$  stabilization.

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## Capacitance

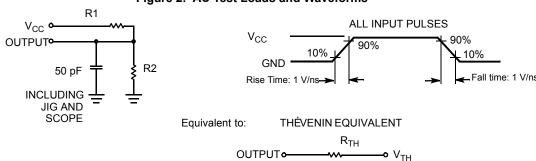
Parameter [7]	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = V_{CC(typ)}$	10	pF
C <sub>OUT</sub>	Output capacitance		10	pF

## **Thermal Resistance**

Parameter [7]	Description	Test Conditions	SOIC	Unit
$\Theta_{JA}$	Thermal resistance (junction to ambient)	Still air, soldered on a 3 x 4.5 inch, four-layer printed circuit board	55	°C/W
$\Theta_{\sf JC}$	Thermal resistance (junction to case)		22	°C/W

## **AC Test Loads and Waveforms**

Figure 2. AC Test Loads and Waveforms



Parameters	2.5 V (2.2 V – 2.7 V)	3.0 V (2.7 V – 3.6 V)	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R <sub>TH</sub>	8000	645	Ω
V <sub>TH</sub>	1.20	1.75	V



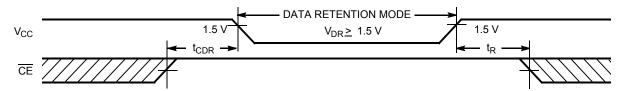
## **Data Retention Characteristics**

Over the Operating Range

Parameter	Description	Conditions	Min	<b>Typ</b> <sup>[6]</sup>	Max	Unit
$V_{DR}$	V <sub>CC</sub> for data retention		1.5	-	-	V
I <sub>CCDR</sub>	Data retention current	$V_{CC} = 1.5 \text{ V}, \overline{CE} \ge V_{CC} - 0.2 \text{ V},$	-		6	μА
		$V_{IN} \ge V_{CC} - 0.2 \text{ V or } V_{IN} \le 0.2 \text{ V}$				
t <sub>CDR</sub> <sup>[7]</sup>	Chip deselect to data retention time		0	-	_	ns
t <sub>R</sub> <sup>[8]</sup>	Operation recovery time		55	_	_	ns

## **Data Retention Waveform**

Figure 3. Data Retention Waveform



- 6. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25 °C.
- Tested initially and after any design or process changes that may affect these parameters.
   Full Device AC operation requires linear V<sub>CC</sub> ramp from V<sub>DR</sub> to V<sub>CC(min)</sub> ≥ 100 μs or stable at V<sub>CC(min)</sub> ≥ 100 μs.



## **Switching Characteristics**

Over the Operating Range

Parameter [9]	Description	55	ns	11!4
Parameter [8]	Description	Min	Max	Unit
Read Cycle				•
t <sub>RC</sub>	Read cycle time	55	_	ns
t <sub>AA</sub>	Address to data valid	_	55	ns
t <sub>OHA</sub>	Data hold from address change	10	_	ns
t <sub>ACE</sub>	CE LOW to data valid	_	55	ns
t <sub>DOE</sub>	OE LOW to data valid	_	25	ns
t <sub>LZOE</sub>	OE LOW to Low Z [10]	5	_	ns
t <sub>HZOE</sub>	OE HIGH to High Z [10, 11]	_	20	ns
t <sub>LZCE</sub>	CE LOW to Low Z [10]	10	_	ns
t <sub>HZCE</sub>	CE HIGH to High Z [10, 11]	_	20	ns
t <sub>PU</sub>	CE LOW to power-up	0	-	ns
t <sub>PD</sub>	CE HIGH to power-up	_	55	ns
Write Cycle [12	, 13]	•		•
t <sub>WC</sub>	Write cycle time	55	_	ns
t <sub>SCE</sub>	CE LOW to write end	40	-	ns
t <sub>AW</sub>	Address set-up to write end	40	-	ns
t <sub>HA</sub>	Address hold from write end	0	_	ns
t <sub>SA</sub>	Address set-up to write start	0	_	ns
t <sub>PWE</sub>	WE pulse width	40	_	ns
t <sub>SD</sub>	Data set-up to write end	25	_	ns
t <sub>HD</sub>	Data hold from write end	0	_	ns
t <sub>HZWE</sub>	WE LOW to High Z [10, 11]	_	20	ns
t <sub>LZWE</sub>	WE HIGH to Low Z [10]	10	_	ns

<sup>9.</sup> Test Conditions for all parameters other than three-state parameters assume signal transition time of 3 ns or less (1 V/ns), timing reference levels of V<sub>CC(typ)</sub>/2, input pulse levels of 0 to  $V_{CC(typ)}$ , and output loading of the specified  $I_{OL}/I_{OH}$  as shown in the Figure 2 on page 5.

<sup>10.</sup> At any given temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZOE</sub> is less than t<sub>LZCE</sub>, and t<sub>HZWE</sub> is less than t<sub>LZWE</sub> for any given device.

<sup>11.</sup> t<sub>HZOE</sub>, t<sub>HZCE</sub>, and t<sub>HZWE</sub> transitions are measured when the output enter a high impedance state.

The internal write time of the memory is defined by the overlap of WE, CE = V<sub>IL</sub>. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.
 The minimum write cycle pulse width for Write Cycle No. 3 (WE controlled, OE LOW) should be equal to the sum of t<sub>SD</sub> and t<sub>HZWE</sub>.



## **Switching Waveforms**

Figure 4. Read Cycle No. 1 (Address Transition Controlled) [14, 15]

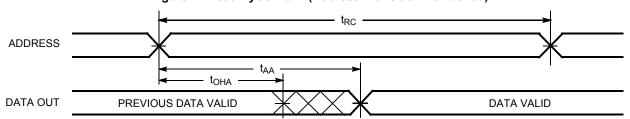
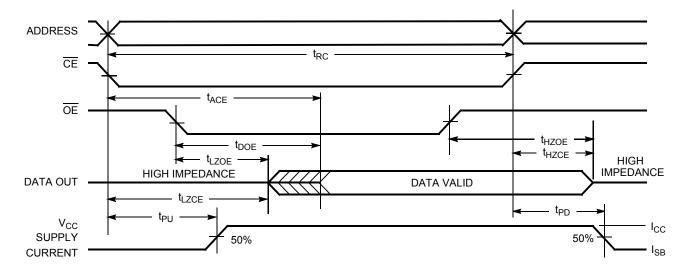


Figure 5. Read Cycle No. 2 (OE Controlled) [15, 16]



#### Notes

<sup>14.</sup> Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE} = V_{IL}$ .

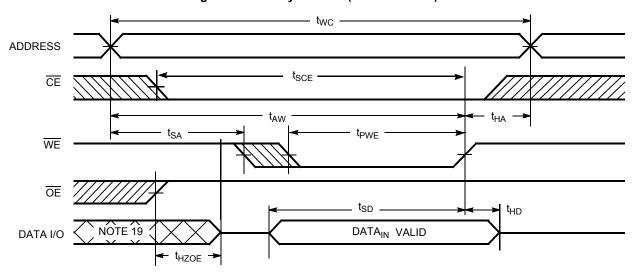
<sup>15.</sup> WE is HIGH for read cycle.

<sup>16.</sup> Address valid prior to or coincident with  $\overline{\text{CE}}$  transition LOW.



## Switching Waveforms (continued)

Figure 6. Write Cycle No. 1 (WE Controlled) [17, 18]



<sup>17.</sup> Data I/O is high impedance if  $\overline{OE} = V_{IH}$ .

<sup>18.</sup> If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  HIGH, the output remains in high-impedance state.

<sup>19.</sup> During this period, the I/Os are in output state and input signals should not be applied.



## Switching Waveforms (continued)

Figure 7. Write Cycle No. 2 (CE Controlled) [20, 21]

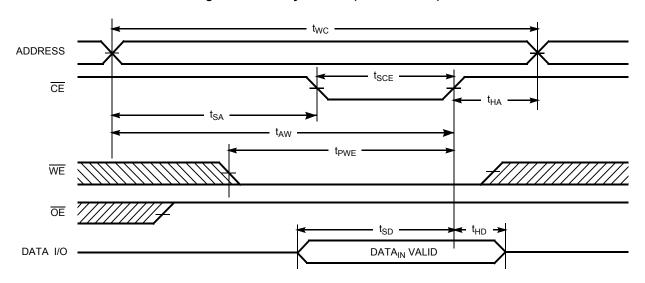
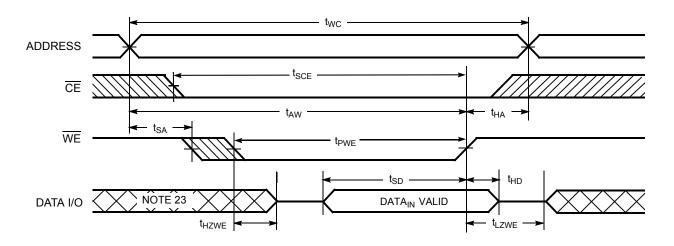


Figure 8. Write Cycle No. 3 (WE Controlled, OE LOW) [21, 22]



#### Notes

- 20. Data I/O is high impedance if OE = V<sub>IH</sub>.
  21. If CE goes HIGH simultaneously with WE HIGH, the output remains in high-impedance state.
- 22. The minimum write cycle pulse width should be equal to the sum of  $t_{\text{SD}}$  and  $t_{\text{HZWE}}$ .
- 23. During this period, the I/Os are in output state and input signals should not be applied.



## **Truth Table**

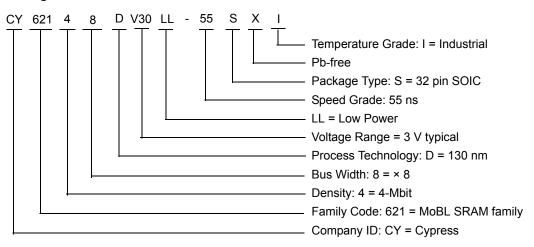
CE	WE	OE	Inputs/Outputs	Mode	Power
Н	Х	Х	High Z	Deselect/Power-down	Standby (I <sub>SB</sub> )
L	Н	L	Data out (I/O <sub>0</sub> -I/O <sub>7</sub> )	Read	Active (I <sub>CC</sub> )
L	Н	Н	High Z	Output disabled	Active (Icc)
L	L	Х	Data in (I/O <sub>0</sub> -I/O <sub>7</sub> )	Write	Active (Icc)

## **Ordering Information**

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
55	CY62148DV30LL-55SXI	51-85081	32-pin SOIC (Pb-free)	Industrial

Contact your local Cypress sales representative for availability of these parts.

### **Ordering Code Definitions**

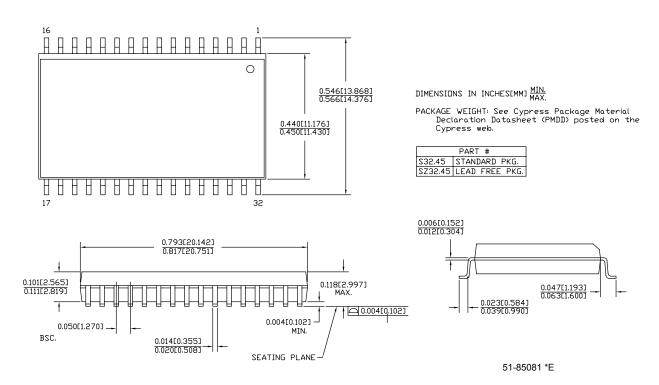


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## **Package Diagrams**

Figure 9. 32-pin SOIC (450 Mils) Package Outline, 51-85081





## **Acronyms**

Acronym	Description			
CMOS	Complementary Metal Oxide Semiconductor			
I/O	Input/Output			
MoBL	More Battery Life			
SOIC	Small-Outline Integrated Circuit			
SRAM	Static Random Access Memory			

## **Document Conventions**

## **Units of Measure**

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μΑ	microampere			
mA	milliampere			
ns	nanosecond			
pF	picofarad			
V	volt			
W	watt			



## **Document History Page**

	Pocument Number: 38-05341  Pocument Number: 38-05341  Pocument Number: 38-05341  Pocument Number: 38-05341					
Rev.	ECN No.	Issue Date	Change	Description of Change		
**	127480	06/17/03	HRT	Created new data sheet		
*A	131041	01/23/04	CBD	Changed from Advance to Preliminary		
*B	222180	See ECN	AJU	Changed from Preliminary to Final Added 70 ns speed bin Modified footnote #6 and #12 Removed MAX value for V <sub>DR</sub> on "Data Retention Characteristics" table Modified input and output capacitance values Added Pb-free ordering information Removed 32-pin STSOP package		
*C	498575	See ECN	NXR	Added Automotive-A Operating Range Removed SOIC package from Product Offering Updated Ordering Information Table		
*D	729917	See ECN	VKN	Added SOIC package and its related information Updated Ordering Information Table		
*E	2896036	03/19/10	AJU	Added Table of Contents. Removed inactive parts from Ordering Information. Updated Packaging Information Updated links in Sales, Solutions, and Legal Information.		
*F	3166059	02/08/2011	RAME	Removed Automotive related info Removed 70 ns speed bin related info Remove TSOP and VFBGA package related info Added Ordering Code Definitions. Added Acronyms and Units of Measure. Updated to new template.		
*G	4315741	03/20/2014	VINI	Updated Package Diagrams: spec 51-85081 – Changed revision from *C to *E. Updated to new template. Completing Sunset Review.		
*H	4576406	01/16/2015	VINI	Added related documentation hyperlink in page 1. Updated Switching Characteristics: Added Note 13 and referred the same note in "Write Cycle". Updated Switching Waveforms: Added Note 22 and referred the same note in Figure 8.		
*	4702987	03/27/2015	VINI	Updated Maximum Ratings: Referred Notes 3, 4 in "Supply voltage to ground potential". Completing Sunset Review.		
*K	5975781	11/24/2017	AESATMP8	Updated logo and Copyright.		



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